2023년 2월 14일(화), 10:55-12:25
Room L (다이아몬드 II, 6층)

G. Device & Process Modeling, Simulation and Reliability 분과
[TL2-G] TCAD Simulation and Reliability

좌장: 이재우 교수(고려대학교)

TL2-G-1 **10:55-11:25** **[초청]**	**Toward Realistic Plasma Process Modeling and Simulation** Jae-Hyeong Park[1], Won-Seok Chang[2], Hae-Sung You[1], Deuk-Chul Kwon[2], Jung Sik Yoon[2], and Yeon-Ho Im[1] *[1]School of Semiconductor and Chemical Engineering, Jeonbuk National University, [2]Plasma Technology Research Center, Korea Institute of Fusion Energy*
TL2-G-2 **11:25-11:40**	**FDSOI-Based Polarity Gate-Less Reconfigurable FET** Dong Hyeok Lee[1] and Jiwon Chang[2] *[1]Department of Materials Science and Engineering, Yonsei University, [2]Department of System Semiconductor Engineering, Yonsei University*
TL2-G-3 **11:40-11:55**	**Global Variability in 2-levels Stacked Nanowire Gate-All-Around Field Effect Transistor** Donghyun Kim[1,2], Sylvain Barraud[3], Gerard Ghibaudo[1], Christoforos Theodorou[1], and Jae Woo Lee[2] *[1]Université Grenoble Alpes, Université Savoie Mont Blanc, Grenoble INP, CNRS, IMEP-LAHC, [2]Department of Electronics and Information Engineering, Korea University, [3]Université Grenoble Alpes, CEA, LETI*
TL2-G-4 **11:55-12:10**	**Mechanism of Gate Oxide Breakdown for Highly Doped Carbon Transistor** N.-J. Kim, G.-J. Kim, S. Lee, N.-H. Lee, YC. Hwang, and HS. Kim *Memory Division, Samsung Electronics Co., Ltd.*
TL2-G-5 **12:10-12:25**	**Frequency-Dependent Kink Effect in Floating Body PD-SOI MOSFETs** Kyeongjun Kim and Seonghearn Lee *Department of Electronics Engineering, Hankuk University of Foreign Studies*